WANGFENG ELECTRON

旺峰电子

RB751V40T1G

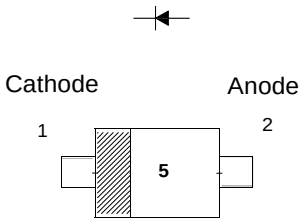
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

Applications

- High speed switching



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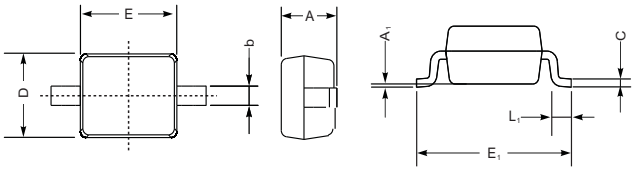
SOD323



UNIT		A	C	D	E	E_1	b	L_1	A_1
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—
mil	max	43	5.9	55	70	108	16	16	8
	min	32	3.1	47	63	100	9.8	7.9	—

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

Parameter	Symbol	Limit	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	0.03	A
Non-repetitive Peak Forward Surge Current@t=8.3ms	I_{FSM}	0.2	A
Power dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	℃/W
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55~+150	℃

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Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA	V_F	-	0.37	V
Reverse Current at V_R = 30 V	I_R	-	0.5	μA
Capacitance Between Terminals at V_R = 1 V, f = 1 MHz	C_T	2	-	pF

Note: ESD sensitive product handling required.

RATING AND CHARACTERISTIC CURVES (RB751V40T1G)